

5 é / Descriptions

SOT-23 .> / / x N 3 MOS « | • 'ož

4- CHANNEL MOSFET in a SOT-23 Plastic Package.

α^a / Features $V_{DS} (V) = 30V$ $I_D = 5.5 A (V_{GS} = 20V)$ $R_{DS(ON)} < 31m (V_{GS} = 10V)$ $R_{DS(ON)} < 43m (V_{GS} = 4.5V)$

—)í D }ož HF Product.

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 $9 \cdot \acute{c} \acute{u} \cdot \frac{1}{4} \hat{e} !^2 \grave{o} \cdot o\check{z}$

This device is suitable for use as a load switch or in PWM applications.

Ã W]Ô · / Equivalent Circuit

PIN1 y G

PIN 2 y S

PIN 3 y D

, M V / Marking

@ f Parameter		... Z Symbol	f > Rating	% y Unit
Drain-Source Voltage		V _{DS}	30	V
Drain Current – Continuous		I _D	5.5	A
Pulsed Drain Current		I _{DM}	19	A
Gate-Source Voltage		V _{GS}	±20	V
Total Power Dissipation		P _D	1.4	W
Operating and Storage Junction Temperature Range		T _J , T _{STG}	-55 to 150	
Maximum Junction-to-Ambient	t 0 10s	R _{JJA}	90	/W
Maximum Junction-to-Ambient	Steady-State		125	
		R _{JL}	80	

@ f
Parameter

... Z
Symbol

Symbol
Unit

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Ô ? d • Ž ¢ / Electrical Characteristic Curve

Ø □ =) ¢ / Package Dimensions

, M y f / Marking Instructions

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šWD t...•Žč (x/) / :KSVKXGZ[XK 6XULORK LUX /8 8KLRU] 9URJKXOTM 6

^ačy

1o• Ä ½ “ † 150 ½180 - k ž • 60 ½90sec;

2o• Q > “ † 245 r5 - k ž • 4 Ò 5 r0.5sec;

3o•D N ò i Ò 0 , † 2 ½10 - /sec.

Note:

1.Preheating:150~180 - , Time:60~90sec.

2.Peak Temp.:245 r5 - , Duration:5 r0.5sec.

3. Cooling Speed: 2~10 - /sec.